

SAMYANG ELECTRONICS

(SINGLE CHIP) MBR1020 --- MBR10200

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- $\bigotimes \mathsf{Low}$ forward voltage drop,low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications

MECHANICAL DATA

- - MIL-STD-202,Method 208
- ◇Polarity: As marked
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

	Symbols	MBR 1020	MBR 1030	MBR 1040	MBR 1050	MBR 1060	MBR 1080	MBR 10100	MBR 10150	MBR 10200	Units
Maximum repetitive peak reverse voltage	VRRM	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	Vrms	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage	VDC	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current (see Fig.1)	I(AV)	10.0								Amps	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	FSM	150.0								Amps	
Maximum instantaneous forward voltage at 10.0 A(Note 1)	VF	0. 60			(0.75	0.85		0.90	0.95	Volts
Maximum instantaneous reverse $T_A = 25^{\circ}C$	lr	0.2									•
current at rated DC blocking voltage(Note 1) $T_{A} = 125^{\circ}C$		15 50							mA		
Typical thermal resistance (Note 2)	R_{θ} JC	2.5								°C/W	
Operating junction temperature range	TJ	-65 to+150									°C
Storage temperature range	Tsig	-65 to+150								°C	

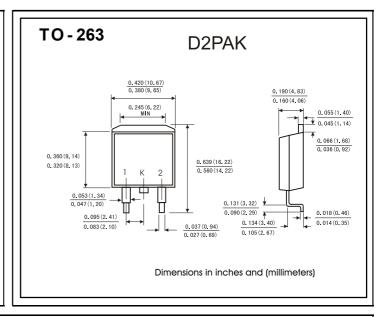
NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

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VOLTAGE RANGE: 20 --- 200 V CURRENT:10.0A



RATINGS AND CHARACTERISTIC CURVES

